

NSDEMP11XV6T1, NSDEMP11XV6T5

Common Anode Quad Array Switching Diode

These Common Anode Epitaxial Planar QUAD Diodes are designed for use in ultra high speed switching applications. The NSDEMP11XV6T1 device is housed in the SOT-563 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast t_{rr}
- Low C_D
- These are Pb-Free Devices

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

| Rating | Symbol | Value | Unit |
|----------------------------|-----------------------|-------|------|
| Reverse Voltage | V_R | 80 | Vdc |
| Peak Reverse Voltage | V_{RM} | 80 | Vdc |
| Forward Current | I_F | 100 | mAdc |
| Peak Forward Current | I_{FM} | 300 | mAdc |
| Peak Forward Surge Current | I_{FSM} (Note 1) | 2.0 | Adc |

THERMAL CHARACTERISTICS

| Characteristic (One Junction Heated) | Symbol | Max | Unit |
|--|-----------------|------------------------------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 357 (Note 2) 2.9 (Note 2) | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 350 (Note 2) | $^\circ\text{C}/\text{W}$ |
| Characteristic (Both Junctions Heated) | Symbol | Max | Unit |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 500 (Note 2) 4.0 (Note 2) | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 250 (Note 2) | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

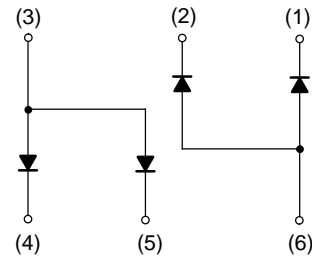
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $t = 1 \mu\text{s}$
2. FR-4 @ Minimum Pad



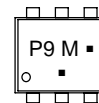
ON Semiconductor®

<http://onsemi.com>



SOT-563
CASE 463A
PLASTIC

MARKING DIAGRAM



P9 = Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|----------------|----------|------------------|
| NSDEMP11XV6T1 | SOT-563* | 4000/Tape & Reel |
| NSDEMP11XV6T1G | SOT-563* | 4000/Tape & Reel |
| NSDEMP11XV6T5 | SOT-563* | 8000/Tape & Reel |
| NSDEMP11XV6T5G | SOT-563* | 8000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

NSDEMP11XV6T1, NSDEMP11XV6T5

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

| Characteristic | Symbol | Condition | Min | Max | Unit |
|---------------------------------|-------------------|--|-----|-----|------------------|
| Reverse Voltage Leakage Current | I_R | $V_R = 70\text{ V}$ | - | 0.1 | μA dc |
| Forward Voltage | V_F | $I_F = 100\text{ mA}$ | - | 1.2 | Vdc |
| Reverse Breakdown Voltage | V_R | $I_R = 100\text{ }\mu\text{A}$ | 0 | - | Vdc |
| Diode Capacitance | C_D | $V_R = 6.0\text{ V}, f = 1.0\text{ MHz}$ | - | 3.5 | pF |
| Reverse Recovery Time | t_{rr} (Note 3) | $I_F = 5.0\text{ mA}, V_R = 6.0\text{ V}, R_L = 100\text{ }\Omega, I_{rr} = 0.1 I_R$ | - | 4.0 | ns |

3. t_{rr} Test Circuit for NSDEMP11XV6T1 in Figure 4.

TYPICAL ELECTRICAL CHARACTERISTICS

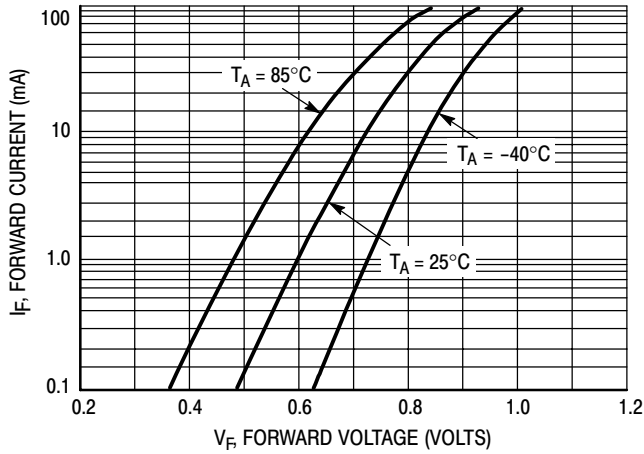


Figure 1. Forward Voltage

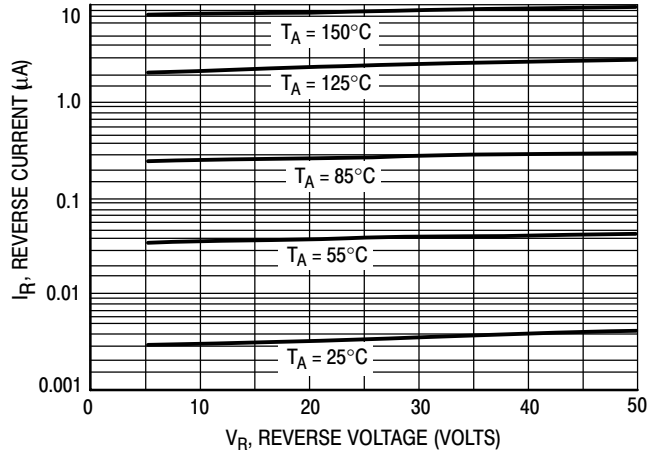


Figure 2. Reverse Current

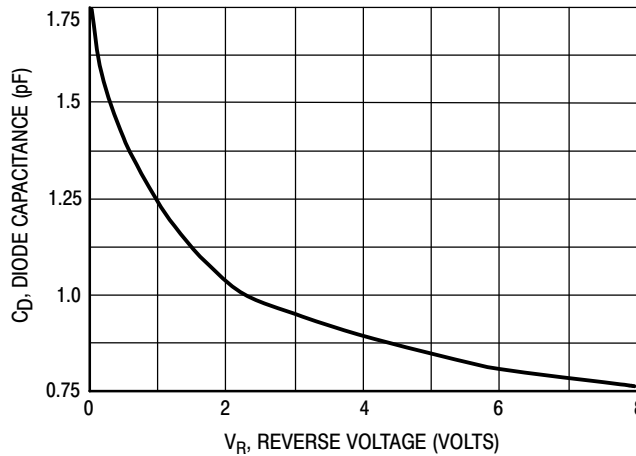


Figure 3. Diode Capacitance

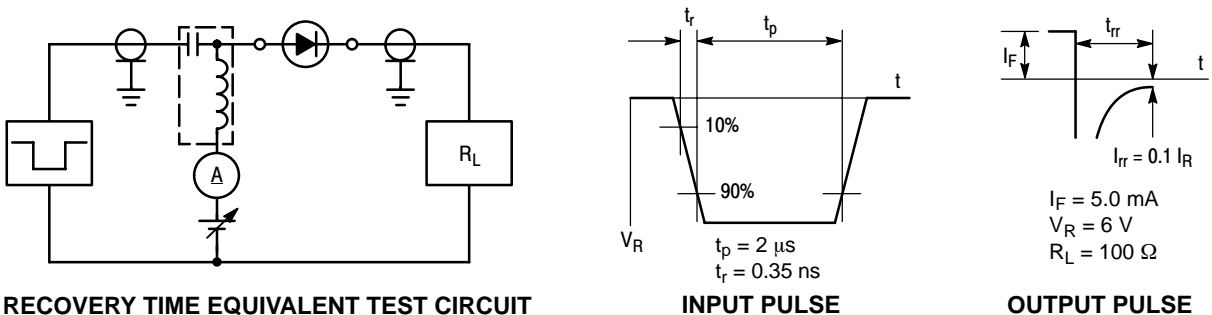
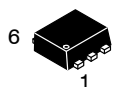


Figure 4. Reverse Recovery Time Test Circuit for the NSDEMP11XV6T1

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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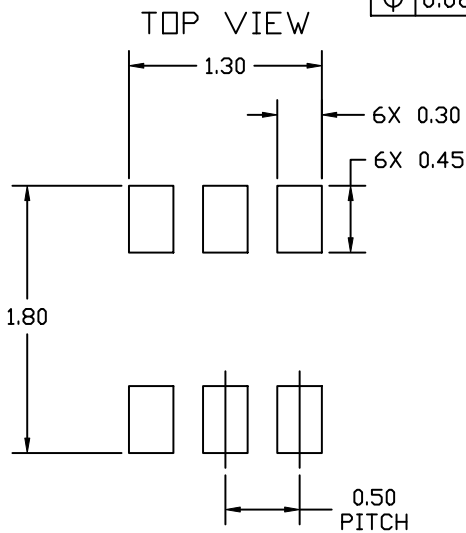
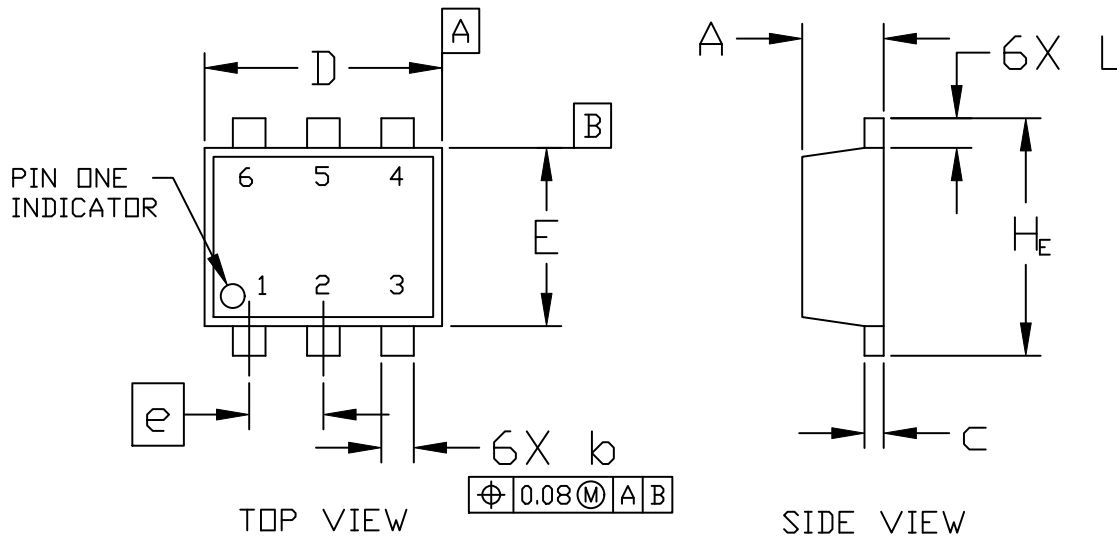
SCALE 4:1

SOT-563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



| DIM | MILLIMETERS | | |
|----------------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.50 | 0.55 | 0.60 |
| b | 0.17 | 0.22 | 0.27 |
| c | 0.08 | 0.13 | 0.18 |
| D | 1.50 | 1.60 | 1.70 |
| E | 1.10 | 1.20 | 1.30 |
| e | 0.50 BSC | | |
| L | 0.10 | 0.20 | 0.30 |
| H _E | 1.50 | 1.60 | 1.70 |

RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ISSUE H

DATE 26 JAN 2021

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

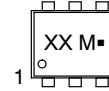
STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Month Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

| | | |
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